Takeshi Noda

List of Publications by Year
in descending order

52	2,437	471371 17	243529 44
papers	citations	h-index	g-index

52	52	52	2808
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Atomic-scale characterization of highly doped Si impurities in GaAs using scanning tunneling microscopy. Applied Surface Science, 2022, 583, 152373.	3.1	0
2	Annealing-Induced Structural Evolution of InAs Quantum Dots on InP (111)A Formed by Droplet Epitaxy. Crystal Growth and Design, 2021, 21, 3947-3953.	1.4	3
3	Highly efficient tin perovskite solar cells achieved in a wide oxygen concentration range. Journal of Materials Chemistry A, 2020, 8, 2760-2768.	5.2	85
4	Efficient and stable tin-based perovskite solar cells by introducing Ï€-conjugated Lewis base. Science China Chemistry, 2020, 63, 107-115.	4.2	160
5	Templated growth of FASnI₃ crystals for efficient tin perovskite solar cells. Energy and Environmental Science, 2020, 13, 2896-2902.	15.6	165
6	Effectiveness of AlGaAs barrier layers as a redistribution channel of photoexcited carriers on anomalous temperature dependence of photoluminescence properties of GaAs quantum dots. Journal of Applied Physics, 2020, 128, 055701.	1.1	2
7	Surface-Controlled Oriented Growth of FASnI3 Crystals for Efficient Lead-free Perovskite Solar Cells. Joule, 2020, 4, 902-912.	11.7	208
8	Efficient and Stable Tin Perovskite Solar Cells Enabled by Graded Heterostructure of Lightâ€Absorbing Layer. Solar Rrl, 2020, 4, 2000240.	3.1	53
9	Highly Reproducible and Efficient FASnI₃ Perovskite Solar Cells Fabricated with Volatilizable Reducing Solvent. Journal of Physical Chemistry Letters, 2020, 11, 2965-2971.	2.1	115
10	Direct observation of charge accumulation in quantum well solar cells by cross-sectional Kelvin probe force microscopy. Applied Physics Letters, 2020, 116, .	1.5	2
11	Highly Stable and Efficient FASnI₃â€Based Perovskite Solar Cells by Introducing Hydrogen Bonding. Advanced Materials, 2019, 31, e1903721.	11.1	266
12	Temperature dependence of Schottky photocurrent for local gate edge illumination in n-AlGaAs/GaAs/AlGaAs double-heterojunction field-effect transistor. Japanese Journal of Applied Physics, 2019, 58, SIIB05.	0.8	0
13	Double-Sided Nonalloyed Ohmic Contacts to Si-doped GaAs for Plasmoelectronic Devices. ACS Omega, 2019, 4, 7300-7307.	1.6	8
14	Cobalt-doped nickel oxide nanoparticles as efficient hole transport materials for low-temperature processed perovskite solar cells. Solar Energy, 2019, 181, 243-250.	2.9	37
15	Coadditive Engineering with 5-Ammonium Valeric Acid Iodide for Efficient and Stable Sn Perovskite Solar Cells. ACS Energy Letters, 2019, 4, 278-284.	8.8	153
16	Study on Carrier Separation in Perovskite Solar Cells by Operando Profiling of Electrical Potential Distribution. Vacuum and Surface Science, 2019, 62, 9-14.	0.0	0
17	Transmission and reflection of charge-density wave packets in a quantum Hall edge controlled by a metal gate. Applied Physics Letters, 2018, 112, .	1.5	3
18	Control of Electrical Potential Distribution for High-Performance Perovskite Solar Cells. Joule, 2018, 2, 296-306.	11.7	138

#	Article	IF	Citations
19	Evidence for a correlated phase of skyrmions observed in real space. Physical Review B, 2018, 98, .	1.1	1
20	Tailoring the Open-Circuit Voltage Deficit of Wide-Band-Gap Perovskite Solar Cells Using Alkyl Chain-Substituted Fullerene Derivatives. ACS Applied Materials & Interfaces, 2018, 10, 22074-22082.	4.0	57
21	Enhanced Photovoltaic Performance of FASnI₃-Based Perovskite Solar Cells with Hydrazinium Chloride Coadditive. ACS Energy Letters, 2018, 3, 1584-1589.	8.8	187
22	Carrier Transfer in Closely Stacked GaAs/AlGaAs Quantum Dots Grown by Using Droplet Epitaxy. Journal of the Korean Physical Society, 2018, 72, 1356-1363.	0.3	0
23	Optically Imaged Striped Domains of Nonequilibrium Electronic and Nuclear Spins in a Fractional Quantum Hall Liquid. Physical Review Letters, 2017, 118, 076802.	2.9	13
24	Thermally Stable MAPbI₃ Perovskite Solar Cells with Efficiency of 19.19% and Area over 1 cm² achieved by Additive Engineering. Advanced Materials, 2017, 29, 1701073.	11.1	541
25	Open-Circuit Voltage in AlGaAs Solar Cells With Embedded GaNAs Quantum Wells of Varying Confinement Depth. IEEE Journal of Photovoltaics, 2017, 7, 162-168.	1.5	5
26	Photoinduced current in n-AlGaAs/GaAs heterojunction field-effect transistor driven by local illumination in edge regions of Schottky metal gate. Japanese Journal of Applied Physics, 2017, 56, 04CG04.	0.8	3
27	Growth of Metamorphic InGaAs on GaAs (111)A: Counteracting Lattice Mismatch by Inserting a Thin InAs Interlayer. Crystal Growth and Design, 2016, 16, 5412-5417.	1.4	15
28	Effects of Ga deposition rate and Sb flux on morphology of GaSb quantum dots formed on GaAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 14, 1600109.	0.8	0
29	Hyperfine-controlled domain-wall motion observed in real space and time. Physical Review B, 2016, 94, .	1.1	4
30	Selective Deposition of Insulating Metal Oxide in Perovskite Solar Cells with Enhanced Device Performance. ChemSusChem, 2015, 8, 2625-2629.	3.6	10
31	Direct visualization of the N impurity state in dilute GaNAs using scanning tunneling microscopy. Nanoscale, 2015, 7, 16773-16780.	2.8	13
32	Lateral current generation in n-AlGaAs/GaAs heterojunction channels by Schottky-barrier gate illumination. Applied Physics Letters, 2015, 106, 022103.	1.5	4
33	Droplet epitaxy growth of telecom InAs quantum dots on metamorphic InAlAs/GaAs(111)A. Japanese Journal of Applied Physics, 2015, 54, 04DH07.	0.8	13
34	Electrical Characteristics of AlGaAs/GaAs Heterostructures With a Pair of 2-D Electron and Hole Channels. IEEE Transactions on Electron Devices, 2015, 62, 3619-3626.	1.6	9
35	Voltage dependence of two-step photocurrent generation in quantum dot intermediate band solar cells. Solar Energy Materials and Solar Cells, 2015, 134, 108-113.	3.0	23
36	Recent developments in droplet epitaxy. , 2014, , .		0

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37	Nitrogen-concentration control in GaNAs/AlGaAs quantum wells using nitrogen Î´-doping technique. , 2014, , .		0
38	Droplet epitaxial growth of highly symmetric quantum dots emitting at telecommunication wavelengths on InP(111)A. Applied Physics Letters, 2014, 104, .	1.5	24
39	Growth of GaSb quantum dots on GaAs (111)A. E-Journal of Surface Science and Nanotechnology, 2014, 12, 304-306.	0.1	0
40	Photo-induced current in n-AlGaAs/GaAs heterojunction channels driven by local illumination at the edge regions of Hall bar. Applied Physics Letters, 2013, 102, 252104.	1.5	2
41	Postâ€growth annealing of GaSb quantum dots in GaAs formed by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1505-1508.	0.8	3
42	Anomalous Capacitanceâ€“Voltage Characteristics of GaAs/AlGaAs Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND07.	0.8	3
43	Currentâ€“Voltage Characteristics of GaAs/AlGaAs Coupled Multiple Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2012, 51, 10ND08.	0.8	5
44	Extension of Absorption Wavelength in GaAs/AlGaAs Quantum Dots with Underlying Quantum Well for Solar Cell Application. Japanese Journal of Applied Physics, 2012, 51, 10ND14.	0.8	2
45	Anisotropic Diffusion of In Atoms from an In Droplet and Formation of Elliptically Shaped InAs Quantum Dot Clusters on (100) GaAs. Crystal Growth and Design, 2011, 11, 726-728.	1.4	17
46	Selfâ€assembled GaAs quantum dots coupled with GaAs wetting layer grown on GaAs (311)A by droplet epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 257-259.	0.8	8
47	Photocurrent characteristics in p-i-n diodes with built-in coupled or uncoupled multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 349-351.	0.8	7
48	Effects of Mg doping on optical and electrical properties of GaNAs multiple quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 420-422.	0.8	3
49	Optical anisotropy of GaSb type-II nanorods on vicinal (111)B GaAs. Applied Physics Letters, 2011, 99, 231901.	1.5	5
50	Optical properties of GaSb/GaAs type-Ð†Ð† quantum dots grown by droplet epitaxy. Applied Physics Letters, 2009, 94, 081911.	1.5	37
51	Ordering of GaAs quantum dots by droplet epitaxy. Physica Status Solidi (B): Basic Research, 2009, 246, 729-732.	0.7	9
52	Growth of GaSb dots on GaAs(100) by droplet epitaxy. Physica Status Solidi (B): Basic Research, 2009, 246, 733-735.	0.7	16